

### Product Description

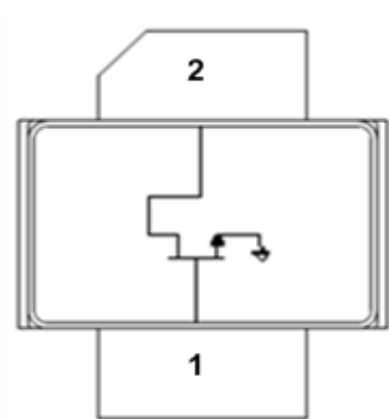
The QPD2195 is a discrete GaN on SiC HEMT which operates from 1.8-2.2 GHz. The device is a single stage pre-matched power amplifier transistor.

The QPD2195 can be used in Doherty architecture for the final stage of a base station power amplifier for macrocell high efficiency systems.

QPD2195 can deliver  $P_{3dB}$  of 400 W at +48 V operation.

RoHS compliant.

### Functional Block Diagram



2 Lead NI780 Package

### Product Features<sup>1</sup>

- Operating Frequency Range: 1.8-2.2 GHz
- Operating Drain Voltage: +48 V
- Maximum Output Power ( $P_{3dB}$ ): 400 W <sup>(1)</sup>
- Maximum Drain Efficiency: 75.4% <sup>(1)</sup>
- Efficiency-Tuned P3dB Gain: 19.1 dB <sup>(1)</sup>
- 2-lead, earless, ceramic flange NI780 package

Note 1: Load pull at 2110 MHz

### Applications

- W-CDMA / LTE
- Macrocell Base Station, B3-B1
- Active Antenna

### Ordering Information

Part Number	Description
QPD2195S2	Box (2 Samples Each)
QPD2195SQ	Tray (25 Samples)
QPD2195SR	Reel (100 Samples)
QPD2195PCB4B01	1805-2170 MHz Evaluation Board



# QPD2195

## 400 W, 48 V, 1.8-2.2 GHz GaN RF Power Transistor

### Absolute Maximum Ratings

Parameter	Value / Range
Gate Current ( $I_G$ )	-67 to 67 mA
Drain Voltage ( $V_D$ )	+55 V
Peak RF Input Power	44 dBm
VSWR Mismatch, P1dB Pulse (10 % duty cycle, 100 $\mu$ width), T = 25 °C	10:1
Storage Temperature	-65 to +150°C

Operation of this device outside the parameter ranges given above may cause permanent damage.

### Recommended Operating

Parameter	Min	Typ	Max	Units
Gate Voltage ( $V_G$ )		-2.8		V
Drain Voltage ( $V_D$ )		48		V
Quiescent Current ( $I_{DQ}$ )		720		mA

Electrical performance is measured under conditions noted in the electrical specifications table. Specifications are not guaranteed over all recommended operating conditions.

### RF Characterization

Parameter	Conditions	Min	Typ	Max	Units
Frequency Range		1805		2170	MHz
Quiescent Current			720		mA
Linear Gain			20.4		dB
P3dB			56.3		dBm
Drain Efficiency	P3dB		70.1		%

Test conditions unless otherwise noted:  $V_D = +48$  V,  $I_{DQ} = 720$  mA, T = 25 °C, Pulsed CW (10% duty cycle, 100  $\mu$ s width) on Class AB single-ended EVB at 1880 MHz

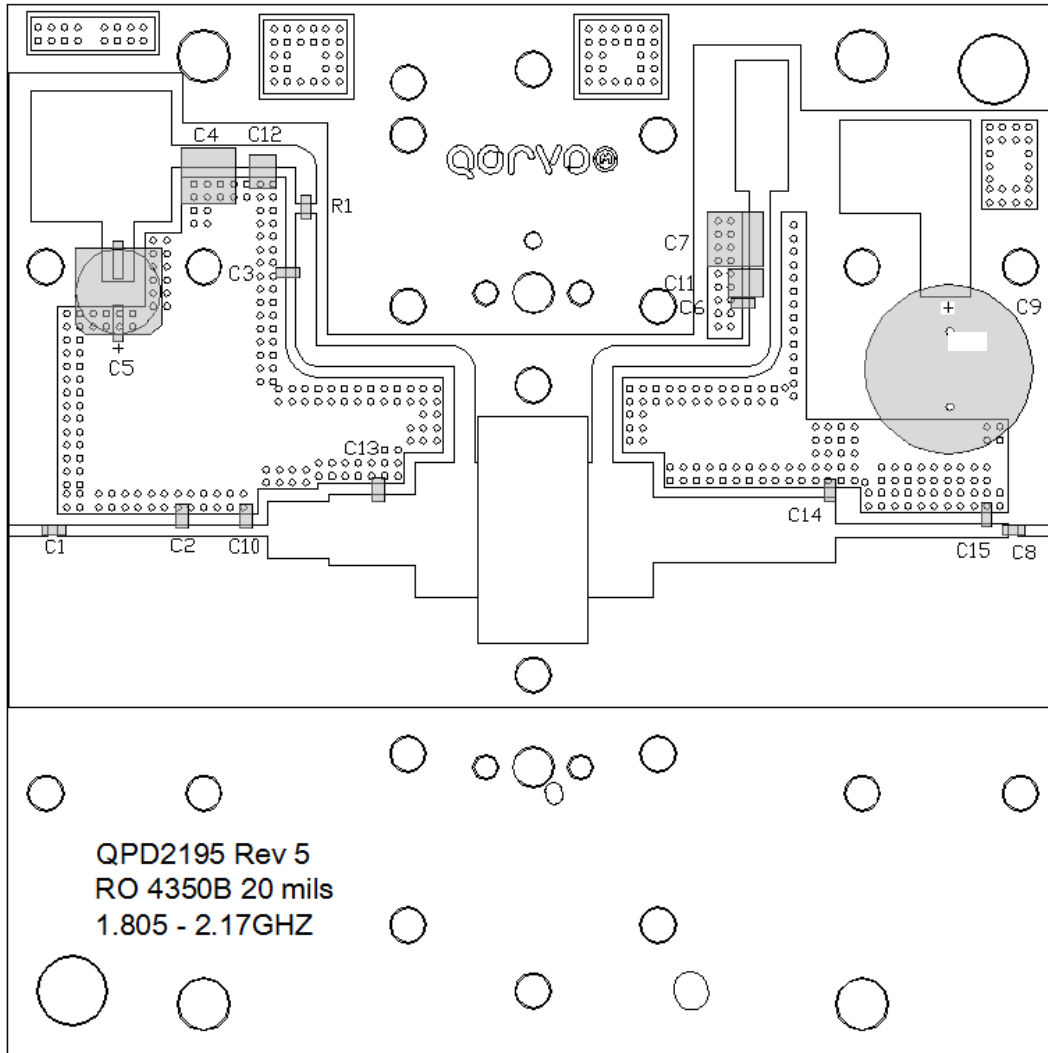
### Thermal and Reliability Information

Parameter	Test Conditions	Value	Units
Thermal Resistance, Peak IR Surface Temperature at Average Power ( $\theta_{JC}$ )	$T_{CASE} = 85^\circ\text{C}$ , $T_{CH} = 110^\circ\text{C}$ , CW: $P_{DISS} = 60$ W, $P_{OUT} = 90$ W	0.42	$^\circ\text{C/W}$

Notes:

1. Thermal resistance measured to package backside.
2. Based on expected carrier amplifier efficiency of Doherty.
3.  $P_{OUT}$  assumes 20% peaking amplifier contribution of total average Doherty rated power.
4. Refer to the following document: [GaN Device Channel Temperature, Thermal Resistance, and Reliability Estimates](#)

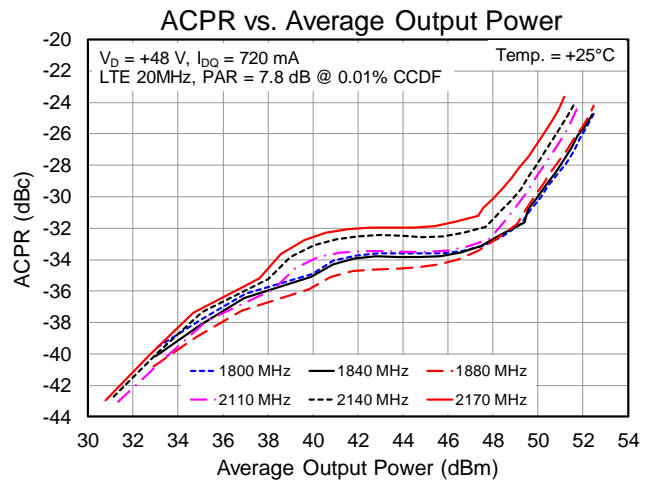
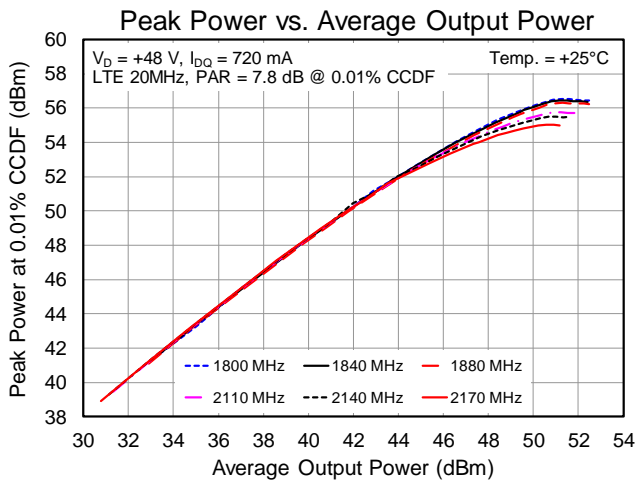
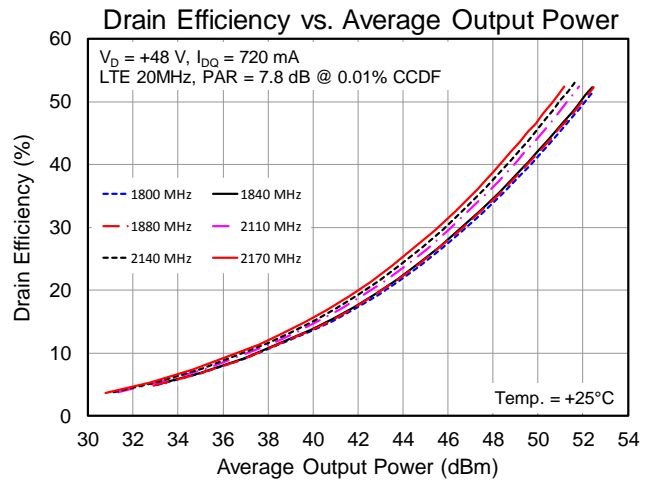
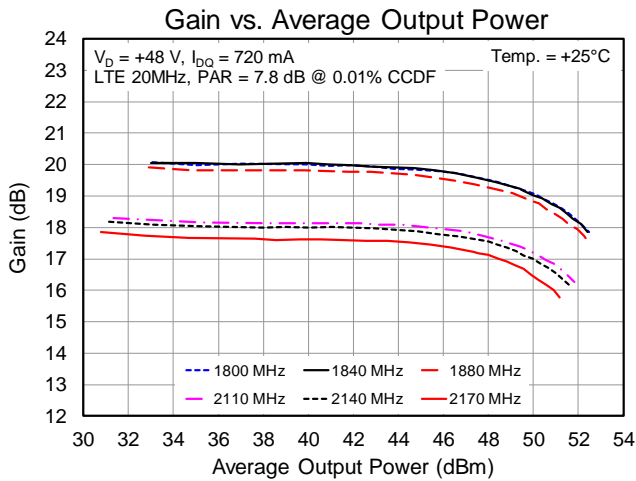
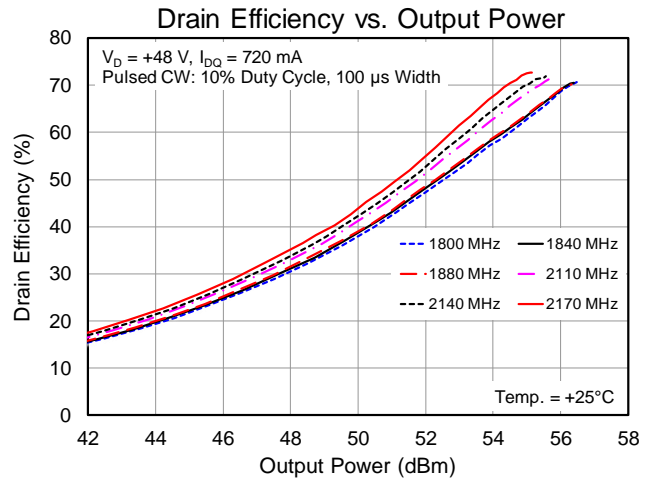
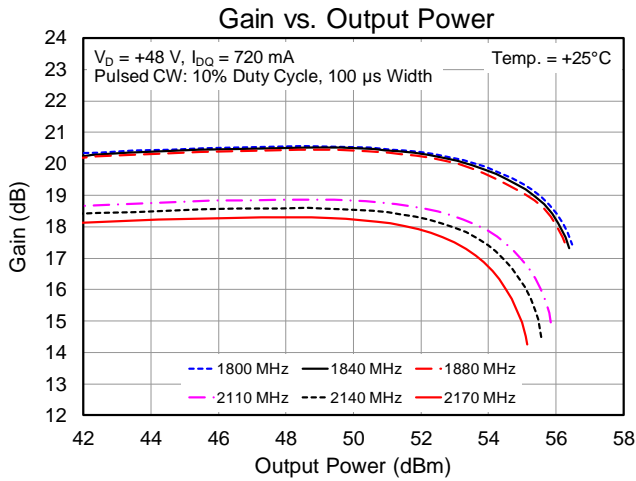
**QPD2195PCB4B01 Layout**



**QPD2195PCB4B01 Bill of Materials**

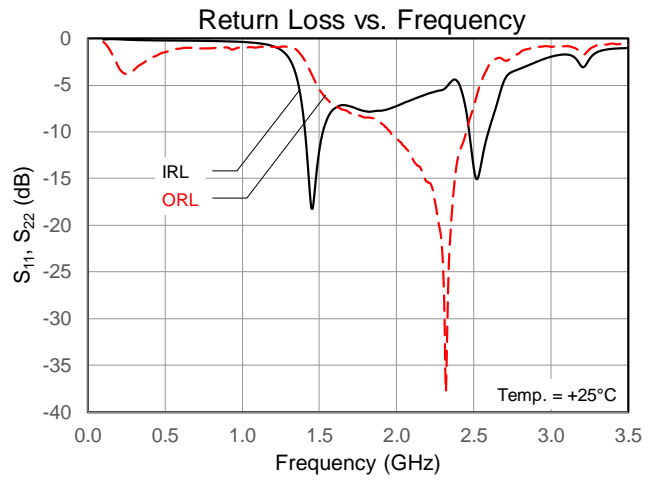
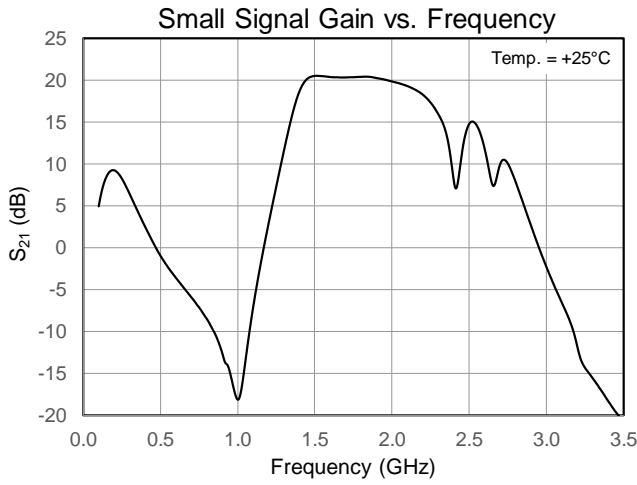
Reference Des.	Value	Description	Manuf.	Part Number
C1, C3, C6, C8	33 pF	Capacitor, 33 pF, 5%, 250V	ATC	ATC800A330JT250X
C2	0.6 pF	Capacitor, 0.6 pF, +/- 0.1pF, 250V	ATC	ATC800A0R6BT250X
C10	0.2 pF	Capacitor, 0.2 pF, +/- 0.1pF, 250V	ATC	ATC800A0R2BT250X
C14, C15	0.4 pF	Capacitor, 0.4 pF, +/- 0.1pF, 250V	ATC	ATC800A0R4BT250X
C13	0.3 pF	Capacitor, 0.3 pF, +/- 0.1pF, 250V	ATC	ATC800A0R3BT250X
C11, C12	1.0 μF	Capacitor, 1 μF, 10%, 100V, X7R	MURATA	GRM32NR72A104KA01L
C4, C7	4.7 μF	Capacitor, 4.7 μF, 10%, 100V, X7R	MURATA	GRM55ER72A475KA01L
C5	100 μF	Capacitor, 100uF, 50V, +/-20%, SMD	Panasonic	EEE-1HA101UAP
C9	220 μF	Capacitor, 220uF, 100V, +/-20%, SMD	Panasonic	AFK227M2AR44T-F
R1	10 Ω	Resistor, 10 Ω, 5%, 0.25W, 1206	Panasonic	ERJ-8ENF10R0V

### QPD2195PCB4B01 Performance Plots



Test conditions unless otherwise noted:  $V_D = +48\text{ V}$ ,  $I_{DQ} = 720\text{ mA}$ ,  $T = 25^\circ\text{C}$ , on Class AB single-ended EVB

## QPD2195PCB4B01 Performance Plots



Test conditions unless otherwise noted:  $V_D = +48\text{ V}$ ,  $I_{BQ} = 720\text{ mA}$ ,  $T = 25^\circ\text{C}$ , on Class AB single-ended EVB

### Power-Tuned Load Pull Performance

Frequency (MHz)	Source Impedance	Load Impedance	Gain @ P3dB (dB)	P3dB (dBm)	Drain Efficiency (%)
1800	1.68 – j2.21	5.39 – j1.33	18.2	56.0	60.5
1840	1.34 – j2.45	5.39 – j1.33	18.1	56.1	62.7
1880	1.44 - j2.82	5.54 - j0.11	17.8	56.2	60.9
1990	1.51 – j3.72	5.79 + j1.48	17.4	56.0	60.4
2110	2.00 – j5.57	3.89 + j3.09	17.2	56.0	60.5
2140	2.48 – j6.14	3.67 + j3.42	16.7	56.0	59.5
2170	3.07 - j6.71	3.67 + j3.42	16.6	56.1	61.8
2200	3.38 – j7.21	3.11 + j3.04	16.6	55.9	58.5

Test conditions unless otherwise noted:  $V_D = +48$  V,  $I_{DQ} = 720$  mA,  $T = 25^\circ\text{C}$ , Pulsed (10% duty cycle, 100  $\mu\text{s}$  width)

### Efficiency-Tuned Load Pull Performance

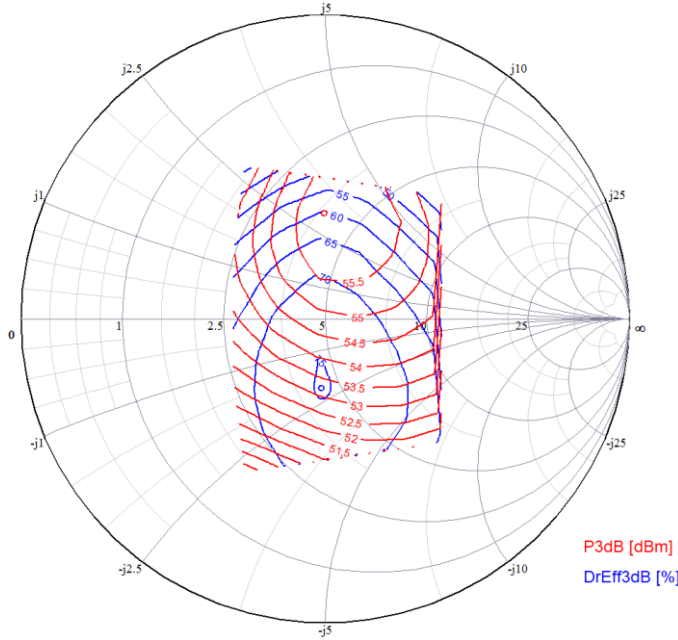
Frequency (MHz)	Source Impedance	Load Impedance	Gain @ P3dB (dB)	P3dB (dBm)	Drain Efficiency (%)
1800	1.68 – j2.21	1.79 – j1.97	20.3	53.5	72.6
1840	1.34 – j2.45	1.79 – j1.97	20.2	53.2	73.3
1880	1.44 - j2.82	1.79 - j1.97	19.9	53.1	73.9
1990	1.51 – j3.72	3.10 – j1.88	19.4	53.9	74.1
2110	2.00 – j5.57	4.36 – j2.15	19.1	53.2	75.4
2140	2.48 – j6.14	4.40 – j2.03	18.8	53.0	75.5
2170	3.07 - j6.71	5.70 - j2.55	18.4	53.0	77.4
2200	3.38 – j7.21	6.74 – j1.27	18.4	53.6	75.5

Test conditions unless otherwise noted:  $V_D = +48$  V,  $I_{DQ} = 720$  mA,  $T = 25^\circ\text{C}$ , Pulsed (10% duty cycle, 100  $\mu\text{s}$  width)

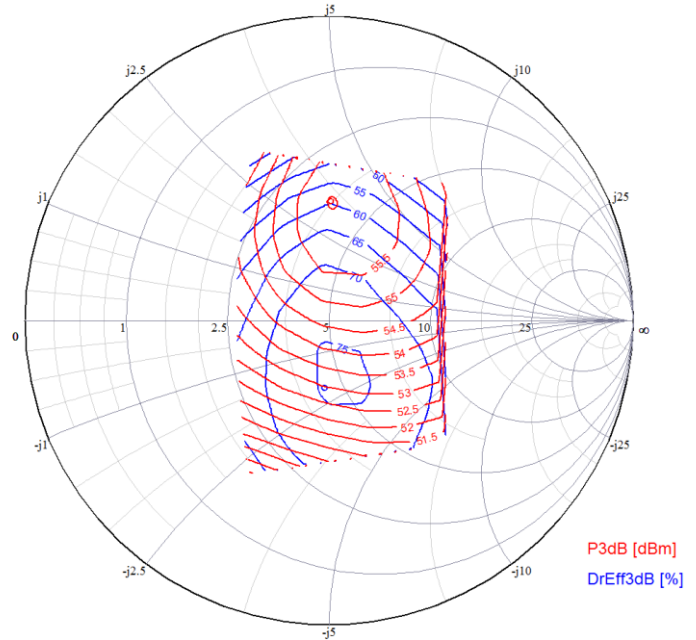


## Load Pull Plots

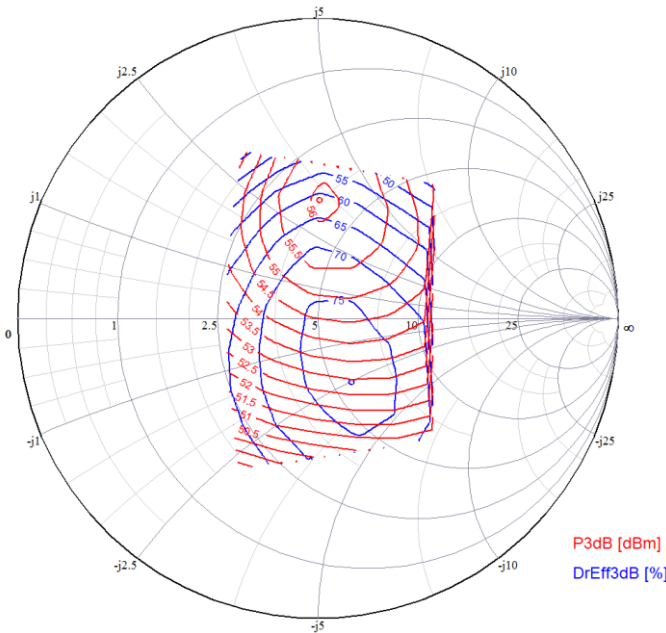
Load Pull at 2.11 GHz



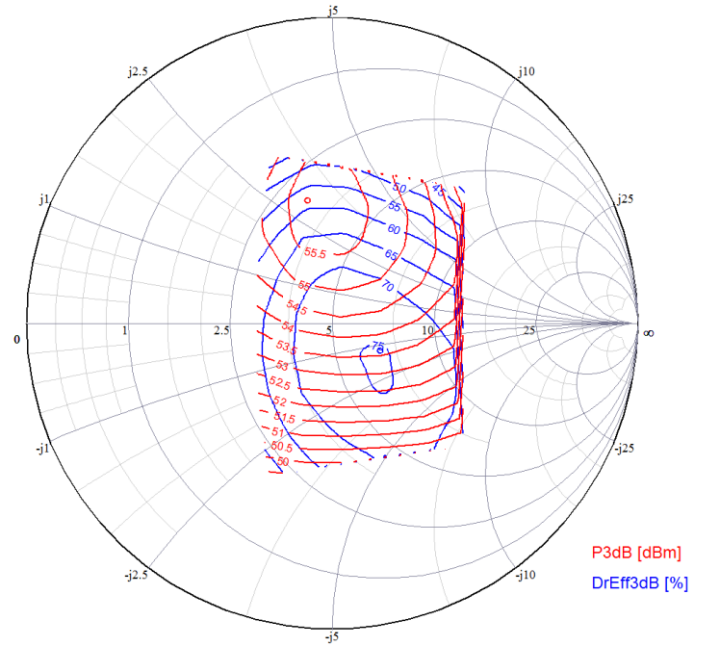
Load Pull at 2.14 GHz



Load Pull at 2.17 GHz

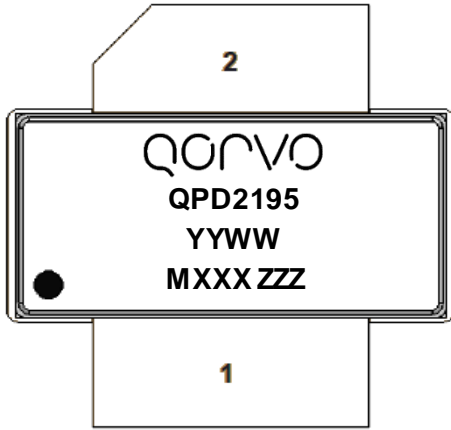


Load Pull at 2.2 GHz

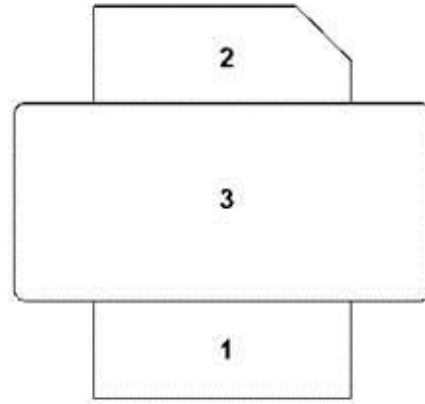


Test conditions unless otherwise noted:  $V_D = +48\text{ V}$ ,  $I_{DQ} = 720\text{ mA}$ ,  $T = 25^\circ\text{C}$ , Pulsed (10% duty cycle, 100  $\mu\text{s}$  width)

### Pin Configuration



TOP VIEW



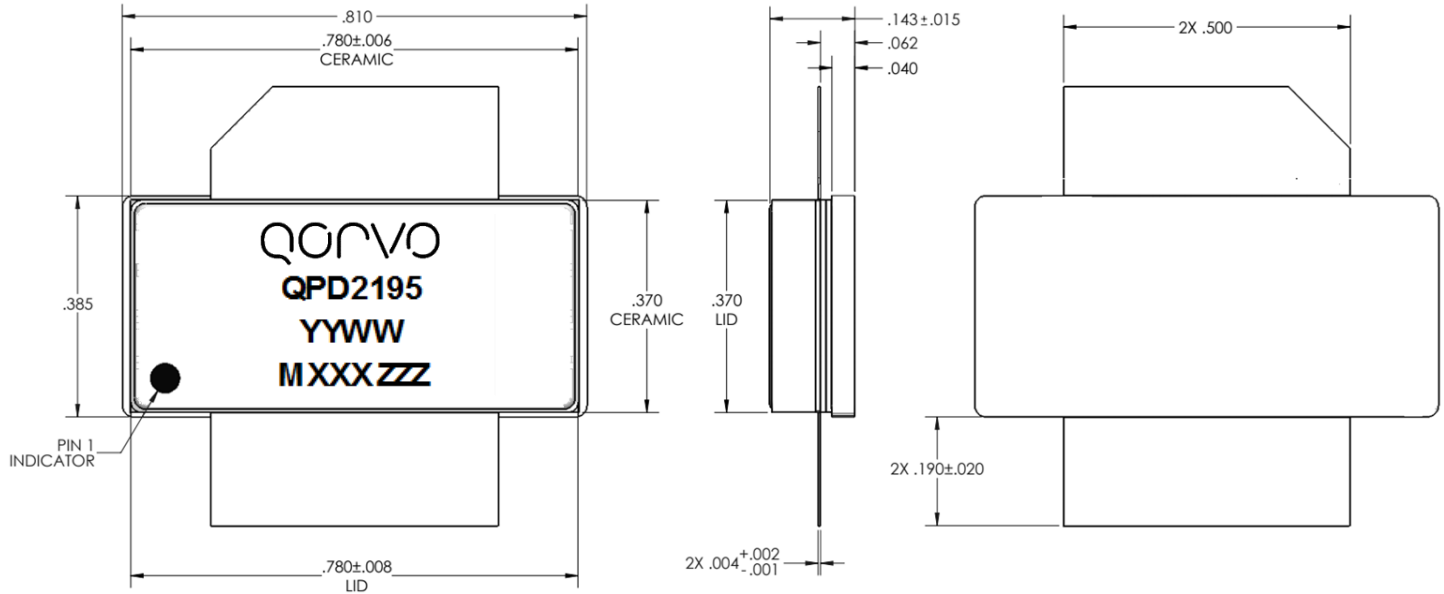
BOTTOM VIEW

### Pin Description

Pin No.	Label	Description
1	RF IN, VG	RF Input, Gate Bias
2	RF OUT, VD	RF Output, Drain Bias
3 (Backside Paddle)	RF/DC GND	RF/DC Ground

## Package Marking and Dimensions

Marking: Qorvo Logo  
 Part Number – QPD2195  
 Date Code – YYWW  
 Production Lot Number – MXXX  
 Serial Number – ZZZ



Notes: Unless Otherwise Specified;

1. Material:  
 Package Base: Metal/Ceramic  
 Package Lid: Ceramic  
 Lead: Alloy 42
2. Package exposed metal base and leads are NiAu plated. Au thickness is minimum 60  $\mu\text{m}$ .
3. Part is epoxy sealed.
4. Part meets industry NI780 footprint.
5. Body dimensions do not include lid shift or epoxy run out, which can be up to 0.020 per side.
6. Dimensions are in inches. General tolerance is  $\pm 0.005$ .

